

***AMENDMENTS TO THE SPECIFICATION***

Please amend the specification as indicated hereafter. It is believed that the following amendments and additions add no new matter to the present application.

***In the Title:***

Please replace the title with the following new title:

**PIEZOELECTRIC ON SEMICONDUCTOR-ON-INSULATOR  
MICROELECTROMECHANICAL RESONATORS**

***In the Specification:*** [Use ~~striketrough~~ for deleted matter (or double square brackets “[[ ]]” if the striketrough is not easily perceivable, *i.e.*, “4” or a punctuation mark) and underlined for added matter.]

**Please amend paragraph [0002] starting on p. 1, as follows:**

This application is related to copending U.S Utility patent application entitled “Capacitive Resonators and Methods of Fabrication,” ~~doeket~~ Ser. No. 62020.1440 10/632,176, filed on the same date.

**Please amend paragraph [0004] starting on p. 1, as follows:**

The present invention is generally related to MEMS (micro-electro-mechanical systems) technology, and, more particularly, is related to piezoelectric resonators ~~and methods of fabricating the same.~~

**Please amend paragraph [0009] starting on p. 2, as follows:**

Embodiments of the present invention provide ~~[[a]] piezoelectric resonators and methods of fabricating the same.~~

**Please amend paragraph [0010] starting on p. 2, as follows:**

Briefly described, one embodiment of the piezoelectric resonator, among others, includes a resonating member having a bi-directionally adjustable resonance frequency, the resonating member including a semiconductor material of a semiconductor-on-insulator wafer, the semiconductor-on-insulator wafer including an oxide layer adjacent to the semiconductor material and a handle layer adjacent to the oxide layer, the oxide layer disposed between the handle layer and the semiconductor material, an electrode, and a piezoelectric material disposed between the semiconductor material and the electrode, and a capacitor created by the semiconductor material and the handle layer separated by an air gap formed out of the oxide layer, wherein the capacitor is configured to receive a direct current voltage that adjusts the resonance frequency of the resonating member.

**Please amend paragraph [0011] starting on p. 3, as follows:**

~~The present invention can also be viewed as providing methods for fabricating a piezoelectric resonator from a semiconductor-on-insulator substrate. In this regard, one embodiment of such a method, among others, can be broadly summarized by the following steps: forming trenches in a semiconductor layer of the semiconductor-on-insulator substrate; removing an oxide layer from the semiconductor-on-insulator~~

~~substrate; applying a piezoelectric material to the semiconductor layer; and providing an electrode to the piezoelectric material.~~

***In the Abstract:*** [Use ~~striketrough~~ for deleted matter and underlined for added matter.]

Please replace the pending abstract with the newly-submitted abstract attached herewith on a separate sheet.